

Data Sheet September 1998 File Number 475.4

# 2MHz, Operational Transconductance Amplifier (OTA)

The CA3080 and CA3080A types are Gatable-Gain Blocks which utilize the unique operational-transconductance-amplifier (OTA) concept described in Application Note AN6668, "Applications of the CA3080 and CA3080A High-Performance Operational Transconductance Amplifiers".

The CA3080 and CA3080A types have differential input and a single-ended, push-pull, class A output. In addition, these types have an amplifier bias input which may be used either for gating or for linear gain control. These types also have a high output impedance and their transconductance ( $g_M$ ) is directly proportional to the amplifier bias current ( $I_{ABC}$ ).

The CA3080 and CA3080A types are notable for their excellent slew rate ( $50V/\mu s$ ), which makes them especially useful for multiplexer and fast unity-gain voltage followers. These types are especially applicable for multiplexer applications because power is consumed only when the devices are in the "ON" channel state.

The CA3080A's characteristics are specifically controlled for applications such as sample-hold, gain-control, multiplexing, etc.

## **Ordering Information**

PART NUMBER (BRAND)	TEMP. RANGE (°C)	PACKAGE	PKG. NO.	
CA3080A	-55 to 125	8 Pin Metal Can	T8.C	
CA3080AE	-55 to 125	8 Ld PDIP	E8.3	
CA3080AM (3080A)	-55 to 125	8 Ld SOIC	M8.15	
CA3080AM96 (3080A)	-55 to 125	8 Ld SOIC Tape and Reel	M8.15	
CA3080E	0 to 70	8 Ld PDIP	E8.3	
CA3080M (3080)	0 to 70	8 Ld SOIC	M8.15	
CA3080M96 (3080)	0 to 70	8 Ld SOIC Tape and Reel	M8.15	

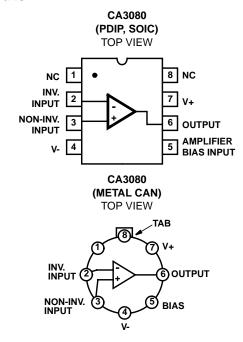
#### **Features**

• Slew Rate (Unity Gain, Compensated) 50V/ $\mu s$
Flexible Supply Voltage Range ±2V to ±15V
• Fully Adjustable Gain 0 to $g_{\mbox{\scriptsize M}}R_{\mbox{\scriptsize L}}$ Limit
• Tight g <sub>M</sub> Spread: - CA3080
Extended q <sub>M</sub> Linearity 3 Decades

## **Applications**

- · Sample and Hold
- Multiplier
- Multiplexer
- Comparator
- · Voltage Follower

#### **Pinouts**



## CA3080, CA3080A

#### **Absolute Maximum Ratings**

Supply Voltage (Between V+ and V- Terminal)
Differential Input Voltage 5V
Input Voltage
Input Signal Current
Amplifier Bias Current (I <sub>ABC</sub> )
Output Short Circuit Duration (Note 1) No Limitation

## **Operating Conditions**

le	mperatur	e Rar	nge			
С	A3080 .			 	 	 0°C to 70°C
С	A3080A			 	 	 -55°C to 125°C

#### **Thermal Information**

Thermal Resistance (Typical, Note 2)	θ <sub>JA</sub> (°C/W)	$\theta_{JC}$ ( $^{o}C/W$ )
PDIP Package	130	N/A
SOIC Package	170	N/A
Metal Can Package	200	120
Maximum Junction Temperature (Metal Can	1)	175°C
Maximum Junction Temperature (Plastic F	Package)	150°C
Maximum Storage Temperature Range	65	<sup>50</sup> C to 150 <sup>0</sup> C
Maximum Lead Temperature (Soldering 1	0s)	300°C
(SOIC - Lead Tips Only)		

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

#### NOTES:

- 1. Short circuit may be applied to ground or to either supply.
- 2.  $\theta_{\mbox{\scriptsize JA}}$  is measured with the component mounted on an evaluation PC board in free air.

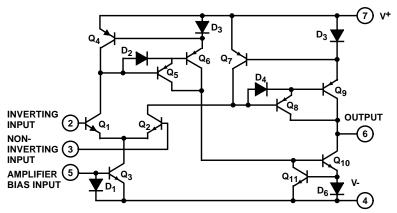
# $\textbf{Electrical Specifications} \qquad \text{For Equipment Design, V}_{SUPPLY} = \pm 15 \text{V, Unless Otherwise Specified}$

PARAMETER		TEST CONDITIONS			CA3080	)				
			TEMP	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
Input Offset Voltage		I <sub>ABC</sub> = 5μA	25	-	0.3	-	-	0.3	2	mV
		I <sub>ABC</sub> = 500μA	25	-	0.4	5	-	0.4	2	mV
			Full	-	-	6	-	-	5	mV
Input Offset Voltage Char	nge	I <sub>ABC</sub> = 500μA to 5μA	25	-	0.2	-	-	0.1	3	mV
Input Offset Voltage Temp	p. Drift	I <sub>ABC</sub> = 100μA	Full	-	-	-	-	3.0	-	μV/ <sup>o</sup> C
Input Offset Voltage	Positive	I <sub>ABC</sub> = 500μA	25	-	-	150	-	-	150	μV/V
Sensitivity	Negative		25	-	-	150	-	-	150	μV/V
Input Offset Current	1	I <sub>ABC</sub> = 500μA	25	-	0.12	0.6	-	0.12	0.6	μА
Input Bias Current		I <sub>ABC</sub> = 500μA	25	-	2	5	-	2	5	μА
			Full	-	-	7	-	-	15	μА
Differential Input Current		I <sub>ABC</sub> = 0, V <sub>DIFF</sub> = 4V	25	-	0.008	-	-	0.008	5	nA
Amplifier Bias Voltage		I <sub>ABC</sub> = 500μA	25	-	0.71	-	-	0.71	-	V
Input Resistance		I <sub>ABC</sub> = 500μA	25	10	26	-	10	26	-	kΩ
Input Capacitance		I <sub>ABC</sub> = 500μA, f = 1MHz	25	-	3.6	-	-	3.6	-	pF
Input-to-Output Capacitar	nce	I <sub>ABC</sub> = 500μA, f = 1MHz	25	-	0.024	-	-	0.024	-	pF
Common-Mode Input-Voltage Range		I <sub>ABC</sub> = 500μA	25	12 to -12	13.6 to -14.6	-	12 to -12	13.6 to -14.6	-	V
Forward Transconductanc	e	I <sub>ABC</sub> = 500μA	25	6700	9600	13000	7700	9600	12000	μS
(Large Signal)			Full	5400	-	-	4000	-	-	μS
Output Capacitance		I <sub>ABC</sub> = 500μA, f = 1MHz	25	-	5.6	-	-	5.6	-	pF
Output Resistance		I <sub>ABC</sub> = 500μA	25	-	15	-	-	15	-	MΩ
Peak Output Current		$I_{ABC} = 5\mu A, R_L = 0\Omega$	25	-	5	-	3	5	7	μА
		$I_{ABC} = 500\mu A, R_L = 0\Omega$	25	350	500	650	350	500	650	μА
			Full	300	-	-	300	-	-	μА

**Electrical Specifications** For Equipment Design,  $V_{SUPPLY} = \pm 15V$ , Unless Otherwise Specified (Continued)

				CA3080		CA3080A				
PARAMETER		TEST CONDITIONS	TEMP	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
Peak Output	Positive	I <sub>ABC</sub> = 5μA, R <sub>L</sub> = ∞	25	-	13.8	-	12	13.8	-	V
Voltage	Negative		25	-	-14.5	-	-12	-14.5	-	V
	Positive	I <sub>ABC</sub> = 500μA, R <sub>L</sub> = ∞	25	12	13.5	-	12	13.5	-	V
	Negative		25	-12	-14.4	-	-12	-14.4	-	V
Amplifier Supply Current		I <sub>ABC</sub> = 500μA	25	0.8	1	1.2	0.8	1	1.2	mA
Device Dissipation		I <sub>ABC</sub> = 500μA	25	24	30	36	24	30	36	mW
Magnitude of Leakage Current		I <sub>ABC</sub> = 0, V <sub>TP</sub> = 0	25	-	0.08	-	-	0.08	5	nA
		I <sub>ABC</sub> = 0, V <sub>TP</sub> = 36V	25	-	0.3	-	-	0.3	5	nA
Propagation Delay		I <sub>ABC</sub> = 500μA	25	-	45	-	-	45	-	ns
Common-Mode Rejection Ratio		I <sub>ABC</sub> = 500μA	25	80	110	-	80	110	-	dB
Open-Loop Bandwidth		I <sub>ABC</sub> = 500μA	25	-	2	-	-	2	-	MHz
Slew Rate	Slew Rate		25	-	75	-	-	75	-	V/μs
		Compensated	25	-	50	-	-	50	-	V/μs

## Schematic Diagram



## **Typical Applications**

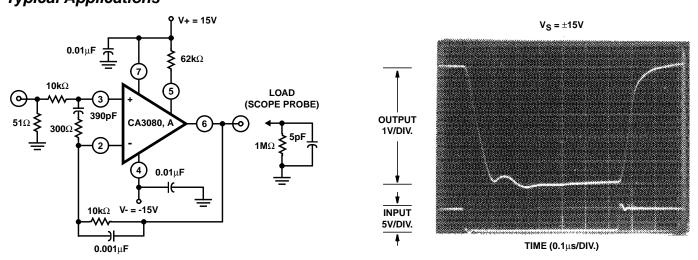


FIGURE 1. SCHEMATIC DIAGRAM OF THE CA3080 AND CA3080A IN A UNITY-GAIN VOLTAGE FOLLOWER CONFIGURATION AND ASSOCIATED WAVEFORM

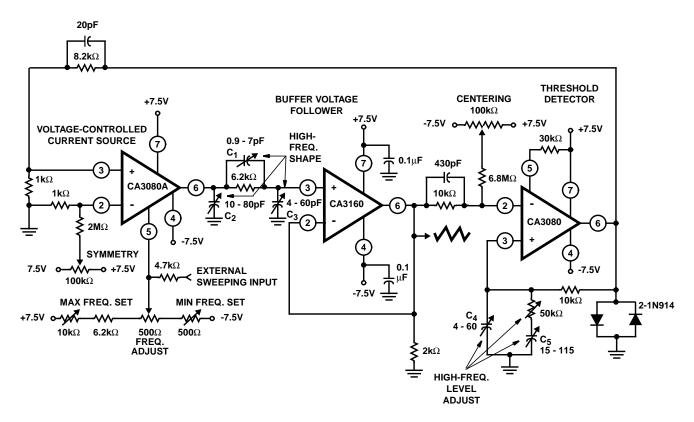
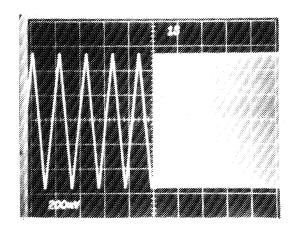
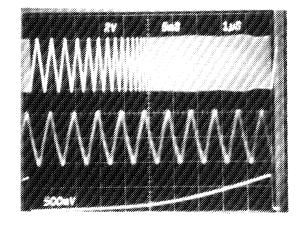


FIGURE 2. 1,000,000/1 SINGLE-CONTROL FUNCTION GENERATOR - 1MHz TO 1Hz



NOTE: A Square-Wave Signal Modulates The External Sweeping Input to Produce 1Hz and 1MHz, showing the 1,000,000/1 frequency range of the function generator.

FIGURE 3A. TWO-TONE OUTPUT SIGNAL FROM THE FUNCTION GENERATOR



NOTE: The bottom trace is the sweeping signal and the top trace is the actual generator output. The center trace displays the 1MHz signal via delayed oscilloscope triggering of the upper swept output signal.

FIGURE 3B. TRIPLE-TRACE OF THE FUNCTION GENERATOR SWEEPING TO 1MHz

FIGURE 3. FUNCTION GENERATOR DYNAMIC CHARACTERISTICS WAVEFORMS

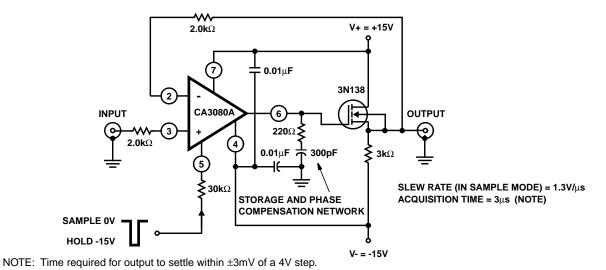


FIGURE 4. SCHEMATIC DIAGRAM OF THE CA3080A IN A SAMPLE-HOLD CONFIGURATION

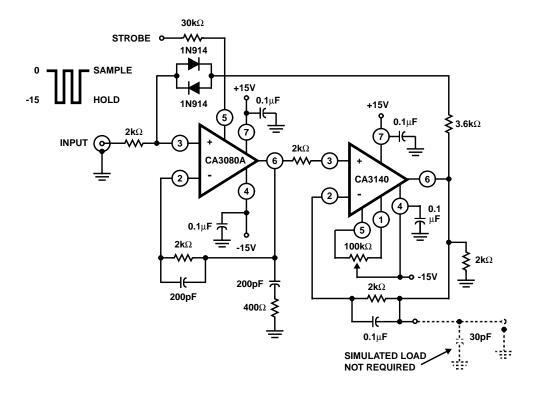
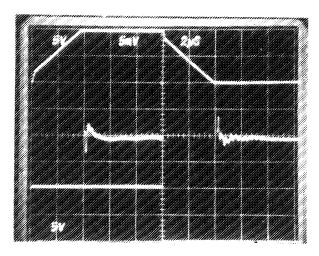


FIGURE 5. SAMPLE AND HOLD CIRCUIT



Top Trace: Output Signal

 $5 V/ Div., \, 2 \mu s/ Div.$ 

Bottom Trace: Input Signal

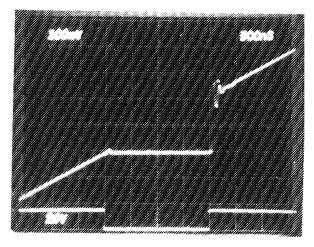
5V/Div., 2μs/Div.

Center Trace: Difference of Input and Output Signals Through

Tektronix Amplifier 7A13

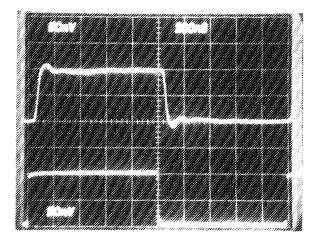
5mV/Div., 2µs/Div.

FIGURE 6. LARGE SIGNAL RESPONSE AND SETTLING TIME FOR CIRCUIT SHOWN IN FIGURE 5



Top Trace: System Output; 100mV/Div., 500ns/Div. Bottom Trace: Sampling Signal; 20V/Div., 500ns/Div.

FIGURE 7. SAMPLING RESPONSE FOR CIRCUIT SHOWN IN FIGURE 5



Top Trace: Output; 50mV/Div., 200ns/Div. Bottom Trace: Input; 50mV/Div., 200ns/Div.

FIGURE 8. INPUT AND OUTPUT RESPONSE FOR CIRCUIT SHOWN IN FIGURE 5

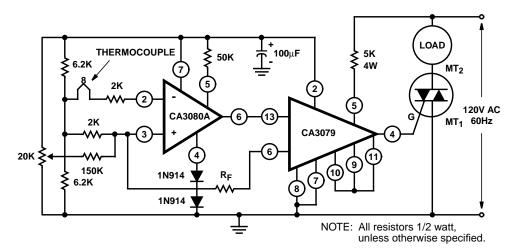


FIGURE 9. THERMOCOUPLE TEMPERATURE CONTROL WITH CA3079 ZERO VOLTAGE SWITCH AS THE OUTPUT AMPLIFIER

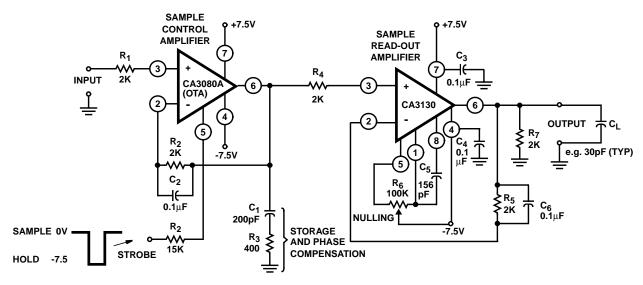
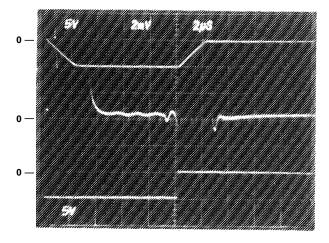


FIGURE 10. SCHEMATIC DIAGRAM OF THE CA3080A IN A SAMPLE-HOLD CIRCUIT WITH BIMOS OUTPUT AMPLIFIER



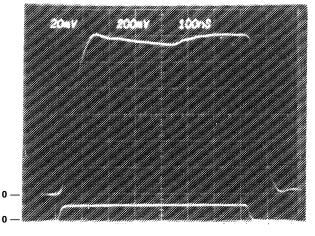
Top Trace: Output; 5V/Div., 2μs/Div.

Center Trace: Differential Comparison of Input and Output

2mV/Div., 2μs/Div.

Bottom Trace: Input; 5V/Div.,  $2\mu s/Div.$ 

FIGURE 11. LARGE-SIGNAL RESPONSE FOR CIRCUIT SHOWN IN FIGURE 10



Top Trace: Output

20mV/Div., 100ns/Div.

Bottom Trace: Input

200mV/Div., 100ns/Div.

FIGURE 12. SMALL-SIGNAL RESPONSE FOR CIRCUIT SHOWN IN FIGURE 10

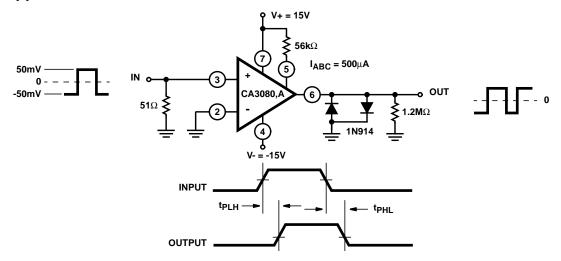


FIGURE 13. PROPAGATION DELAY TEST CIRCUIT AND ASSOCIATED WAVEFORMS

# **Typical Performance Curves**

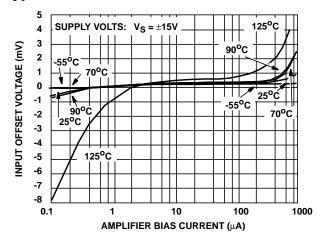


FIGURE 14. INPUT OFFSET VOLTAGE VS AMPLIFIER BIAS CURRENT

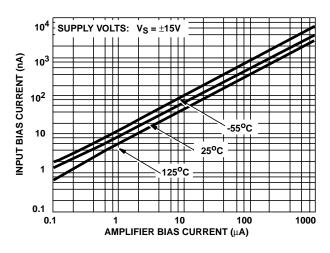


FIGURE 16. INPUT BIAS CURRENT vs AMPLIFIER BIAS CURRENT

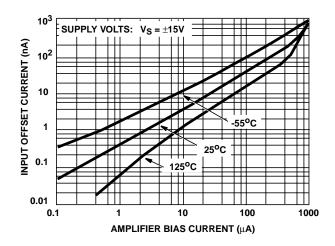


FIGURE 15. INPUT OFFSET CURRENT vs AMPLIFIER BIAS CURRENT

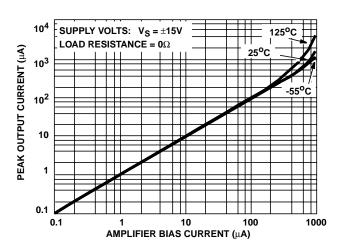


FIGURE 17. PEAK OUTPUT CURRENT VS AMPLIFIER BIAS CURRENT

#### Typical Performance Curves (Continued)

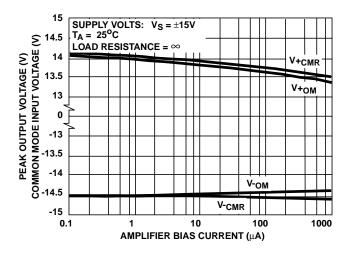


FIGURE 18. PEAK OUTPUT VOLTAGE VS AMPLIFIER BIAS CURRENT

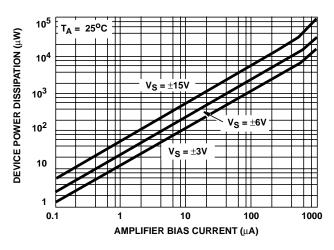


FIGURE 20. TOTAL POWER DISSIPATION vs AMPLIFIER BIAS CURRENT

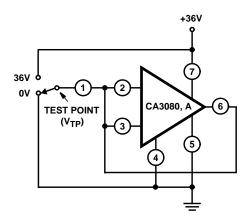


FIGURE 22. LEAKAGE CURRENT TEST CIRCUIT

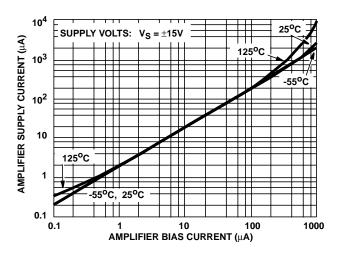


FIGURE 19. AMPLIFIER SUPPLY CURRENT VS AMPLIFIER BIAS CURRENT

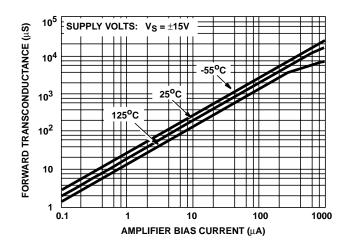


FIGURE 21. TRANSCONDUCTANCE vs AMPLIFIER BIAS CURRENT

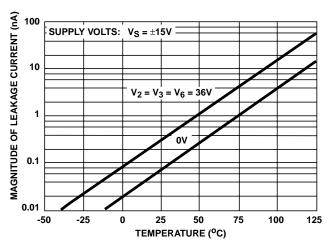


FIGURE 23. LEAKAGE CURRENT vs TEMPERATURE

## Typical Performance Curves (Continued)

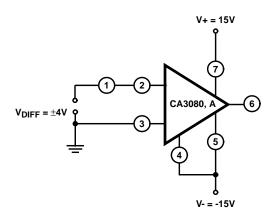


FIGURE 24. DIFFERENTIAL INPUT CURRENT TEST CIRCUIT

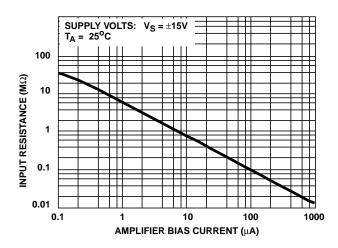


FIGURE 26. INPUT RESISTANCE vs AMPLIFIER BIAS CURRENT

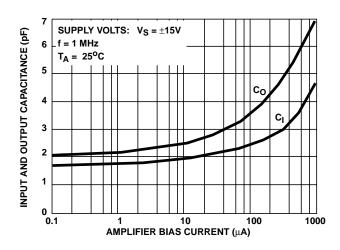


FIGURE 28. INPUT AND OUTPUT CAPACITANCE vs AMPLIFIER BIAS CURRENT

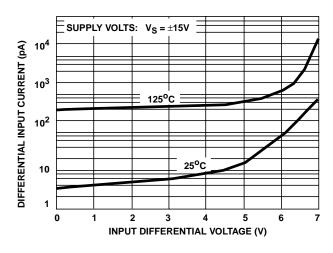


FIGURE 25. INPUT CURRENT vs INPUT DIFFERENTIAL VOLTAGE

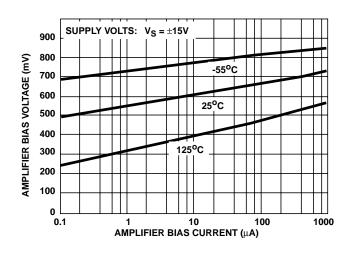


FIGURE 27. AMPLIFIER BIAS VOLTAGE VS AMPLIFIER BIAS CURRENT

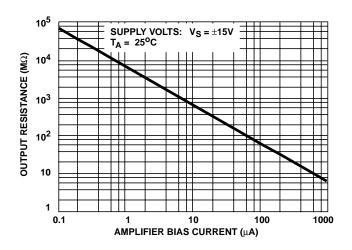


FIGURE 29. OUTPUT RESISTANCE VS AMPLIFIER BIAS CURRENT

## Typical Performance Curves (Continued)

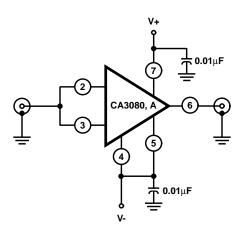


FIGURE 30. INPUT-TO-OUTPUT CAPACITANCE TEST CIRCUIT

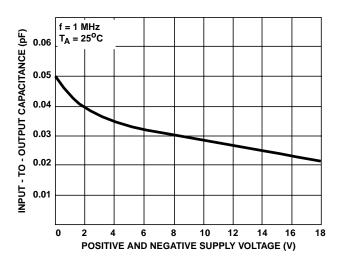


FIGURE 31. INPUT-TO-OUTPUT CAPACITANCE vs SUPPLY VOLTAGE

All Intersil semiconductor products are manufactured, assembled and tested under ISO9000 quality systems certification.

Intersil semiconductor products are sold by description only. Intersil Corporation reserves the right to make changes in circuit design and/or specifications at any time without notice. Accordingly, the reader is cautioned to verify that data sheets are current before placing orders. Information furnished by Intersil is believed to be accurate and reliable. However, no responsibility is assumed by Intersil or its subsidiaries for its use; nor for any infringements of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Intersil or its subsidiaries.

For information regarding Intersil Corporation and its products, see web site www.intersil.com

## Sales Office Headquarters

NORTH AMERICA

Intersil Corporation P. O. Box 883, Mail Stop 53-204 Melbourne, FL 32902

TEL: (321) 724-7000 FAX: (321) 724-7240 **EUROPE** 

Intersil SA Mercure Center 100, Rue de la Fusee 1130 Brussels, Belgium TEL: (32) 2.724.2111

FAX: (32) 2.724.21.11

ASIA

Intersil (Taiwan) Ltd.
7F-6, No. 101 Fu Hsing North Road
Taipei, Taiwan
Republic of China
TEL: (886) 2 2716 9310

FAX: (886) 2 2715 3029